



BAM80

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BAM80** is Designed for VHF AM power amplifier Applications in the range of 100 to 150 MHz.

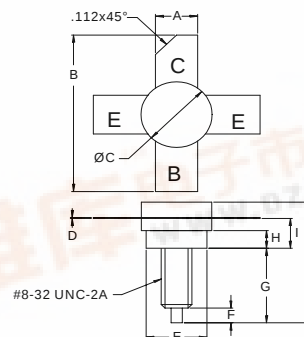
FEATURES:

- Common Emitter
- $P_G = 6.0$ dB at 20 W/150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.5 A
V_{CES}	60 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	85 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	2.0 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CES}	$I_C = 20$ mA	60			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
I_{CES}	$V_{CE} = 30$ V $T_C = 125$ °C			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0		---	---
C_{cb}	$V_{CB} = 28$ V $f = 1.0$ MHz			75	pF
P_G	$V_{CE} = 13.5$ V $P_{OUT} = 20$ W $f = 150$ MHz	6.0	65		dB
η_C					%
VSWR		30:1			---